

# RF Exposure Evaluation

## FCC ID: ZS7-WDXX

### 1. Client Information

**Applicant** : Flastar Technology Co., Ltd.  
**Address** : 3F-4F, 43 Building, Baotian Industrial Zone, Xixiang, Bao'an, Shenzhen, China  
**Manufacturer** : Flastar Technology Co., Ltd.  
**Address** : 3F-4F, 43 Building, Baotian Industrial Zone, Xixiang, Bao'an, Shenzhen, China

### 2. General Description of EUT

<b>EUT Name</b>	:	Wireless Flash Drive	
<b>Models No.</b>	:	WD01, WD02, WD03, WD04, WD05, WD06, WD07, WD08, WD09, WD10	
<b>Model Difference</b>	:	The different models are identical in schematic, structure and critical component, the only different is the appearance.	
<b>Product Description</b>	:	Operation Frequency: 2412MHz~2462MHz	
		Number of Channel:	11 Channels see note (2)
		Out Power	802.11b: 12.90 dBm 802.11g: 11.94dBm 802.11n (20M): 11.69 dBm
		Antenna Gain:	0 dBi Chip Antenna
		Modulation Type:	802.11b: CCK, QPSK, BPSK 802.11g: OFDM 802.11n (20M): OFDM
		Bit Rate of Transmitter:	802.11b:11/5.5/2/1 Mbps 802.11g:54/48/36/24/18/12/9/6 Mbps 802.11n:up to 150Mbps
<b>Power Supply</b>	:	DC Voltage supplied from AC/DC adapter DC Voltage supplied from Li-Polymer battery	
<b>Power Rating</b>	:	AC Adapter: Input: 100~240V 50/60Hz 0.4A Output: 5V 1.5A DC 3.7V 2000mAh from Li-Polymer battery	

More information about the equipment, please refer to the User Manual.

*TB-RF-075-1.0*

## MPE Calculations

1. No Evaluation required if power is below  
( $60/f(\text{GHz}) \text{ mW}$ ) where f is the transmit frequency of the EUT.

2. Calculation:

$$\text{EIRP} = P + G$$

Where P=Conducted Output Power (dBm)

G=Power Gain of the Antenna (dBi)

So

Test Mode	Conducted Power (dBm)	Antenna Gain (dBi)	EIRP (dBm)	EIRP (mW)
802.11b	12.90	0	12.90	19.498
802.11g	11.94	0	11.94	15.632
802.11n(20M)	11.69	0	11.69	14.757

3. Conclusion:

No SAR Evaluation required since Transmitter EIRP is bellow FCC threshold.

### Note

For a more detailed features description, please refer to the RF Test Report.